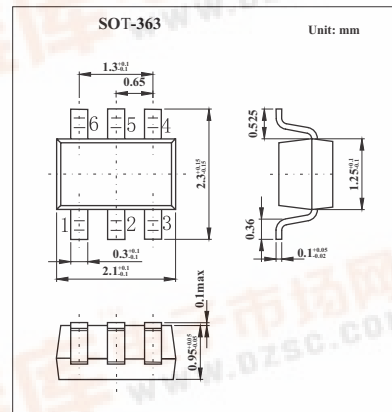


SMD Type Diodes

Silicon Schottky Diode  
BAT62-08S;BAT62-09S

Features

- Low barrier diode for detectors up to GHz frequencies



Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Rating	Unit
Diode reverse voltage	V <sub>RM</sub>	40	V
Forward current	I <sub>F</sub>	20	mA
Total power dissipation; Ts ≤ 105 °C	P <sub>FM</sub>	100	mW
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature range	T <sub>stg</sub>	-55 to +150	°C
Junction - soldering point <sup>1)</sup>	R <sub>thjS</sub>	≤ 450 ≤ tbd	K/W

Note

1.For calculation of R<sub>thJA</sub> please refer to Application Note Thermal Resistance

Electrical Characteristics Ta = 25 °C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current	I <sub>R</sub>	V <sub>R</sub> = 40 V			10	μ A
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 2 mA		0.58	1	V
Forward voltage matching <sup>2)</sup>	ΔV <sub>F</sub>	I <sub>F</sub> = 2 mA			20	mV

Note

2.ΔV<sub>F</sub> is the difference between lowest and highest V<sub>F</sub> in a multiple diode component.

Marking

Type	BAT62-08S	BAT62-09S
Marking	62s	69s

